

**isc Silicon NPN Power Transistor**
**BU500**
**DESCRIPTION**

- High Voltage- $V_{CEX} = 1500V(\text{Min.})$
- Low Collector Saturation Voltage-  
:  $V_{CE(\text{sat})} = 1.0V(\text{Max.}) @ I_C = 4.5A$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

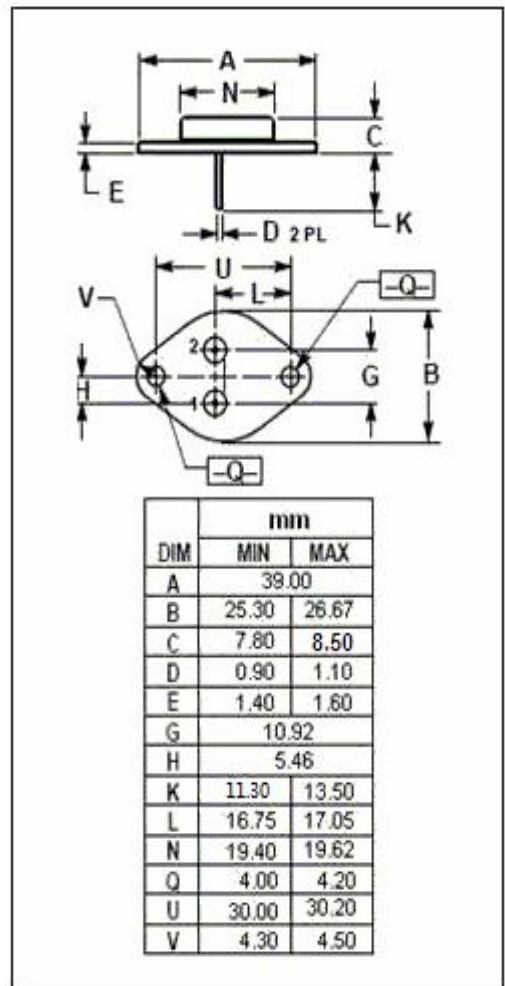
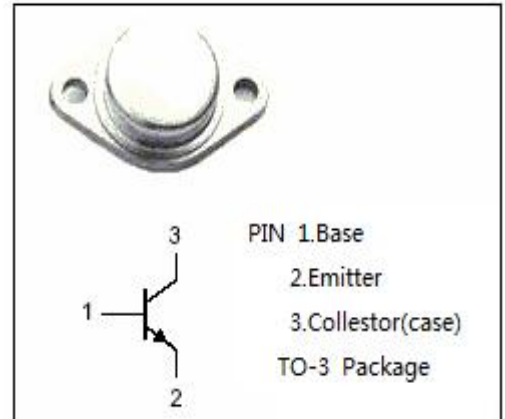
- Designed for use in large screen color deflection circuits .

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1300	V
$V_{CEX}$	Collector-Emitter Voltage	1300	V
$V_{CEO}$	Collector-Emitter Voltage	700	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	6	A
$I_{CM}$	Collector Current-Peak	16	A
$I_B$	Base Current-Continuous	4	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	75	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-65~150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.66	$^\circ\text{C/W}$



## isc Silicon NPN Power Transistor

## BU500

## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	700			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 100mA; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 2A			1.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 4.5A; V <sub>CE</sub> = 2V			1.3	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 1000V; I <sub>E</sub> = 0 V <sub>CB</sub> = 1300V; I <sub>E</sub> = 0			0.02 1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			10	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 4.5A; V <sub>CE</sub> = 5V	3			

## Switching Times

t <sub>s</sub>	Storage Time	I <sub>C</sub> = 4.5A; I <sub>B1</sub> = -I <sub>B2</sub> = 1.5A; V <sub>CC</sub> = 100V			1.2	μs
t <sub>f</sub>	Fall Time				1.0	μs

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